DATA SHEET

BST70A
N-channel vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

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Philips
Semiconductors

PHILIPS

N-channel vertical D-MOS transistor BST70A

DESCRIPTION

N-channel enhancement mode vertical D-MOS transistor in TO-92 variant envelope and intended for use in relay, high-speed and line-transformer drivers.

FEATURES:

- Very low $R_{DS(on)}$
- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No second breakdown

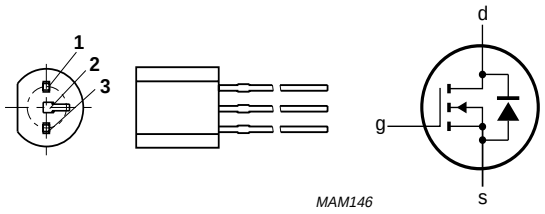
QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	80	V
Gate-source voltage (open drain)	V_{GSO}	max.	20	V
Drain current (DC)	I_D	max.	0.5	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Drain-source ON-resistance				
I_D = 500 mA; V_{GS} = 10 V	$R_{DS(on)}$	typ. max.	2 4	Ω Ω
Transfer admittance				
I_D = 500 mA; V_{DS} = 15 V	$\|Y_{fs}\|$	typ.	300	mS

PINNING - TO-92 VARIANT

1 = source
2 = gate
3 = drain

PIN CONFIGURATION



Note: Various pinout configurations available.

Fig.1 Simplified outline and symbol.

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	80	V
Gate-source voltage (open drain)	V_{GSO}	max.	20	V
Drain current (DC)	I_D	max.	0.5	A
Drain current (peak)	I_{DM}	max.	1.0	A
Total power dissipation up to T_{amb} = 25 °C (note 1)	P_{tot}	max.	1	W
Storage temperature range	T_{stg}	− 65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient (note 1)	$R_{th\ j\text{-}a}$	=	125	K/W

Note

1. Transistor mounted on printed circuit board, max. lead length 4 mm, mounting pad for drain lead min. 10 mm × 10 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage				
I_D = 10 µA; V_{GS} = 0	$V_{(BR)DS}$	min.	80	V
Drain-source leakage current				
V_{DS} = 60 V; V_{GS} = 0	I_{DSS}	max.	1	µA
Gate-source leakage current				
V_{GS} = 20 V; V_{DS} = 0	I_{GSS}	max.	100	nA
Gate threshold voltage				
I_D = 1 mA; V_{DS} = V_{GS}	$V_{GS(th)}$	min.	1.5	V
		max.	3.5	V
Drain-source ON-resistance (see Fig.4)				
I_D = 500 mA; V_{GS} = 10 V	$R_{DS(on)}$	typ.	2.0	Ω
		max.	4.0	Ω
Transfer admittance				
I_D = 500 mA; V_{DS} = 15 V	$\lvert Y_{fs} \rvert$	typ.	300	mS
Input capacitance at f = 1 MHz				
V_{DS} = 10 V; V_{GS} = 0	C_{iss}	typ.	45	pF
		max.	60	pF
Output capacitance at f = 1 MHz				
V_{DS} = 10 V; V_{GS} = 0	C_{oss}	typ.	30	pF
		max.	45	pF
Feedback capacitance at f = 1 MHz				
V_{DS} = 10 V; V_{GS} = 0	C_{rss}	typ.	8	pF
		max.	12	pF
Switching times (see Figs 2 and 3)				
I_D = 500 mA; V_{DS} = 50 V; V_{GS} = 0 to 10 V	t_{on}	max.	10	ns
	t_{off}	max.	15	ns

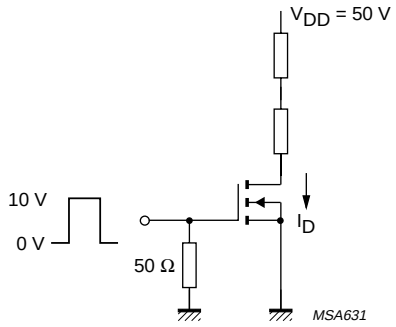


Fig.2 Switching times test circuit.

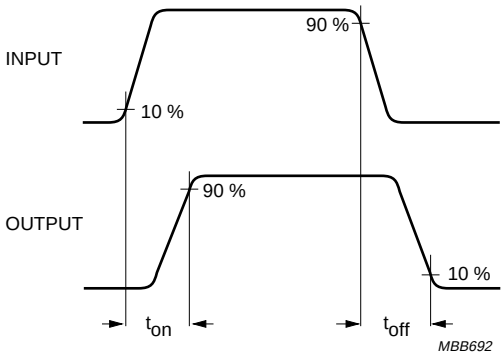


Fig.3 Input and output waveforms.

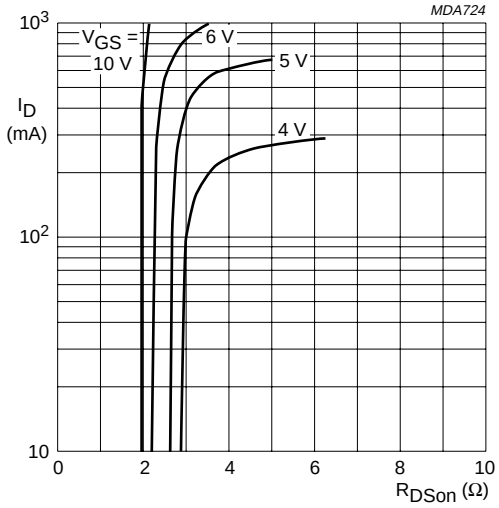


Fig.4 T_j = 25 °C; typical values.

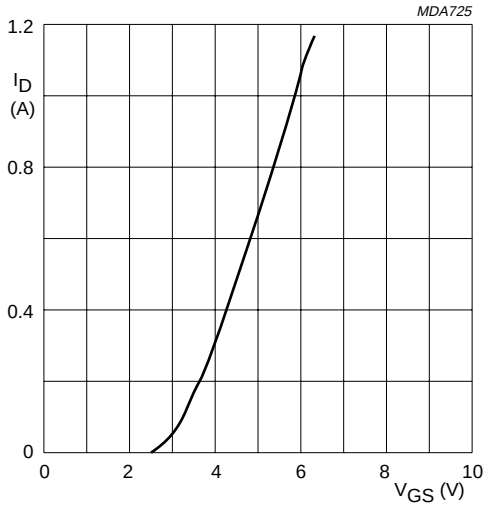


Fig.5 T_j = 25 °C; typical values at V_{DS} = 10 V.

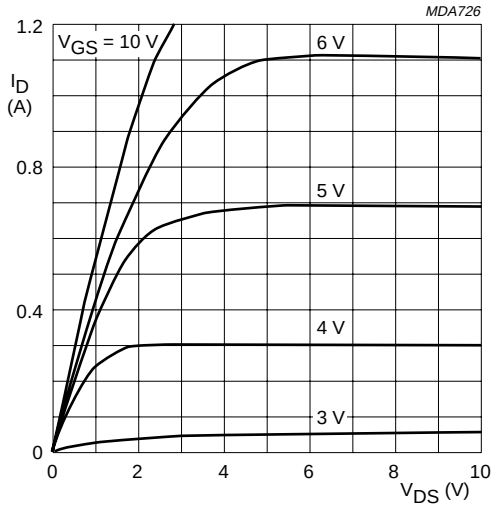


Fig.6 T_j = 25 °C; typical values.

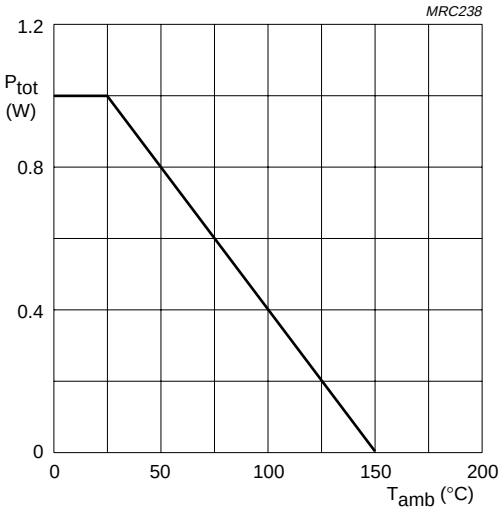


Fig.7 Power derating curve.

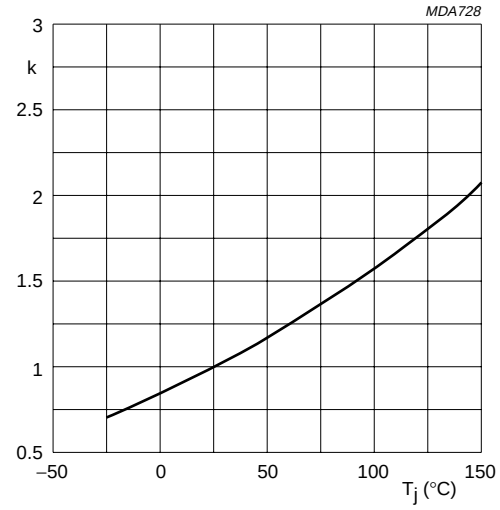


Fig.8

$$k = \frac{R_{DS\,(on)} \text{ at } T_j}{R_{DS\,(on)} \text{ at } 25\ °C};$$

typ. values at 500 mA/10 V.

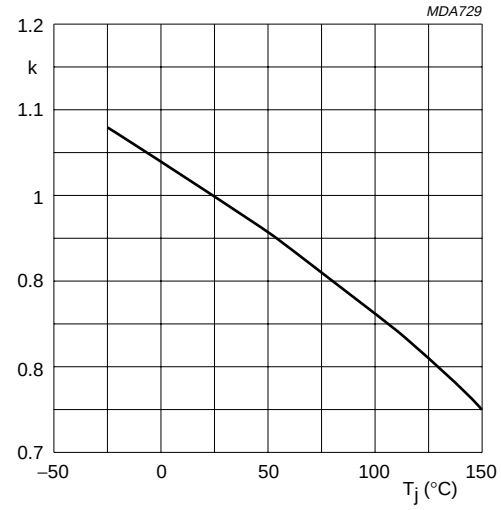


Fig.9

$$k = \frac{V_{GS\,(th)} \text{ at } T_j}{V_{GS\,(th)} \text{ at } 25\ °C};$$

$V_{GS(th)}$ at 1 mA; typical values.

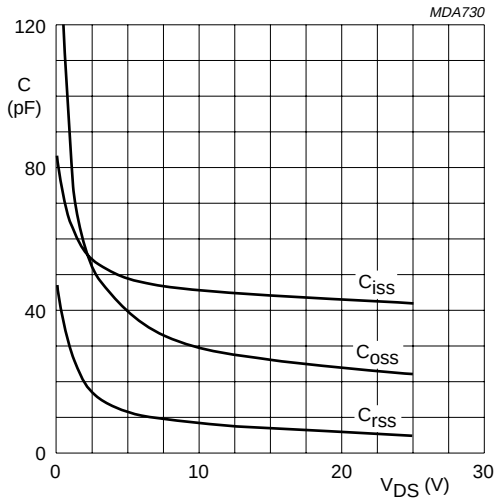
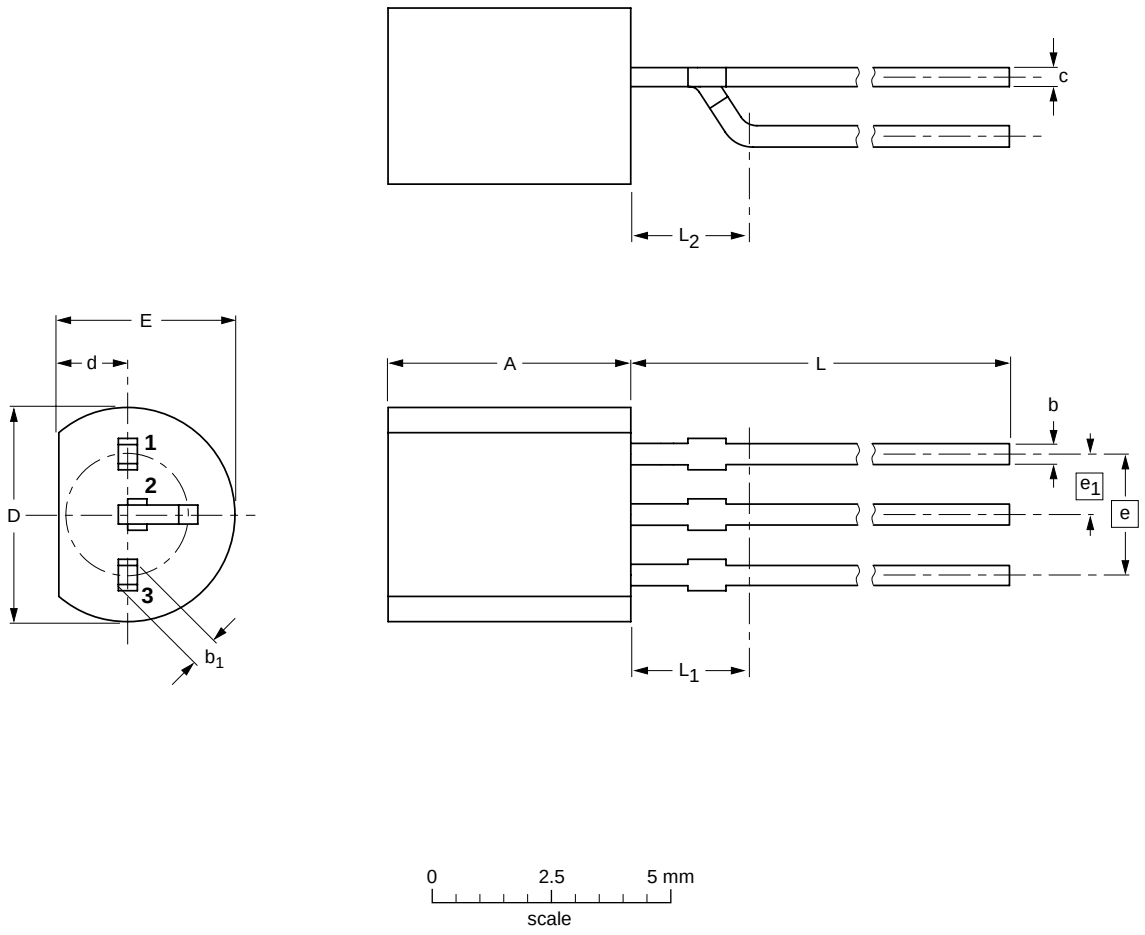


Fig.10 T_j = 25 °C; V_{GS} = 0; f = 1 MHz; typical values.

PACKAGE OUTLINES

Plastic single-ended leaded (through hole) package; 3 leads (on-circle) **SOT54 variant**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1 (1) max	L_2 max
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	2.5

Notes

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT54 variant		TO-92	SC-43			97-04-14

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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